



# Standard Rectifier Module

$$V_{RRM} = 2 \times 1200 \text{ V}$$

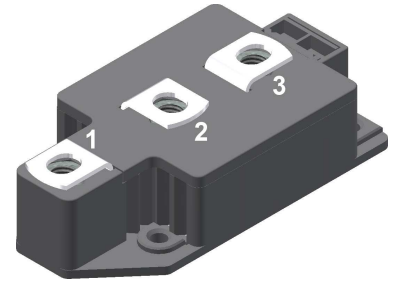
$$I_{FAV} = 300 \text{ A}$$

$$V_F = 1 \text{ V}$$

Phase leg

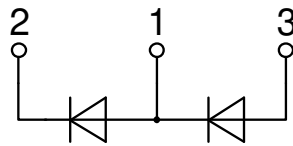
Part number

**MDD310-12N1**



Backside: isolated

E72873



### Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

### Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

### Package: Y2

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

### Disclaimer Notice

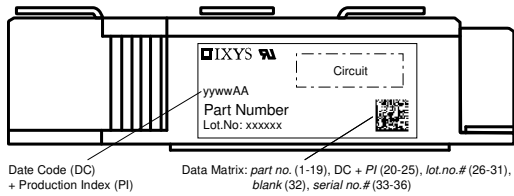
Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).



Rectifier				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM}$	max. non-repetitive reverse blocking voltage				1300	V	
$V_{RRM}$	max. repetitive reverse blocking voltage				1200	V	
$I_R$	reverse current	$V_R = 1200\text{ V}$			1	mA	
		$V_R = 1200\text{ V}$			20	mA	
$V_F$	forward voltage drop	$I_F = 300\text{ A}$			1.13	V	
		$I_F = 600\text{ A}$			1.33	V	
		$I_F = 300\text{ A}$	$T_{VJ} = 125^\circ\text{C}$			1.00	V
		$I_F = 600\text{ A}$	$T_{VJ} = 125^\circ\text{C}$			1.29	V
$I_{FAV}$	average forward current	$T_C = 100^\circ\text{C}$			300	A	
$I_{F(RMS)}$	RMS forward current	180° sine			480	A	
$V_{F0}$	threshold voltage	} for power loss calculation only			0.75	V	
$r_F$	slope resistance				0.63	mΩ	
$R_{thJC}$	thermal resistance junction to case				0.13	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.04		K/W	
$P_{tot}$	total power dissipation				960	W	
$I_{FSM}$	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^\circ\text{C}$		11.5	kA	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		12.4	kA	
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^\circ\text{C}$		9.78	kA	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		10.6	kA	
$I^2t$	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^\circ\text{C}$		661.3	kA <sup>2</sup> s	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		641.7	kA <sup>2</sup> s	
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^\circ\text{C}$		477.8	kA <sup>2</sup> s	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		463.5	kA <sup>2</sup> s	
$C_J$	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$		381	pF	



Package Y2			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			600	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				254		g
$M_D$	mounting torque		2.5		5	Nm
$M_T$	terminal torque		12		15	Nm
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	13.0			mm
$d_{Spb/Apb}$		terminal to backside	13.0			mm
$V_{ISOL}$	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDD310-12N1	MDD310-12N1	Box	2	429155

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 150^{\circ}C$

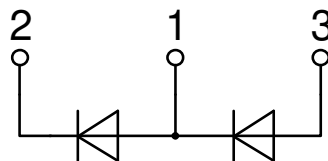
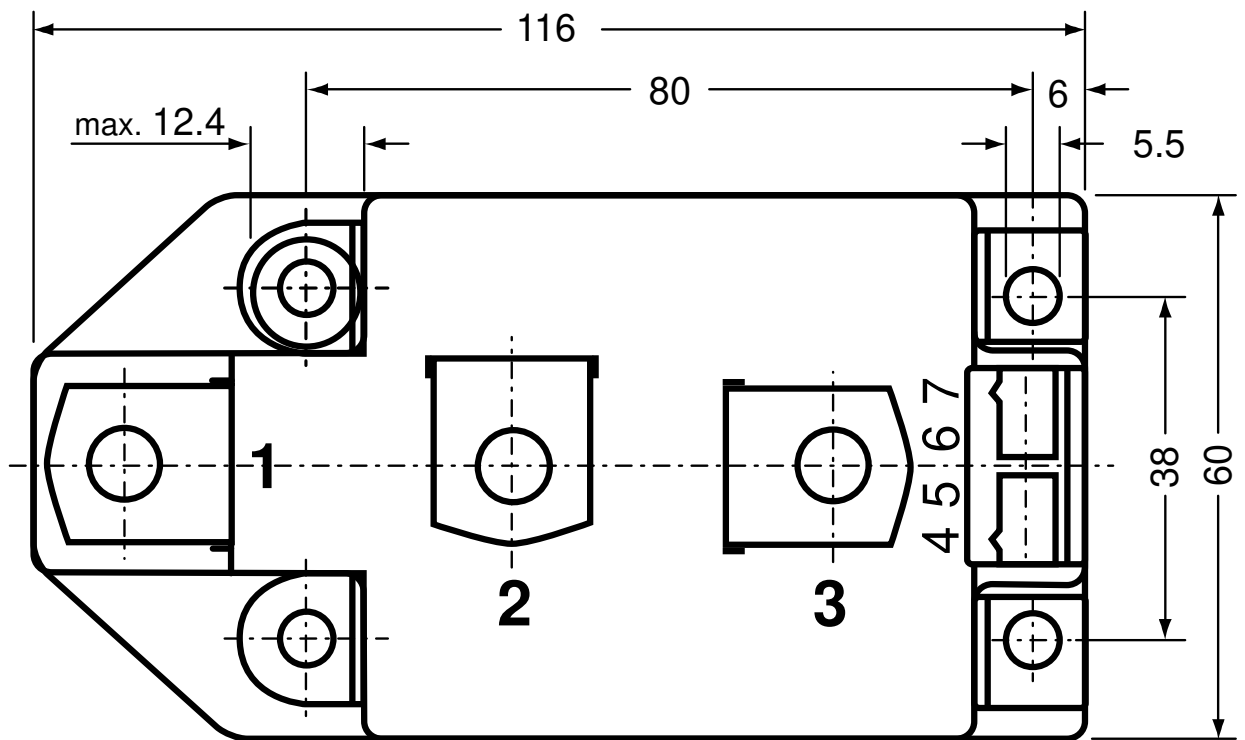
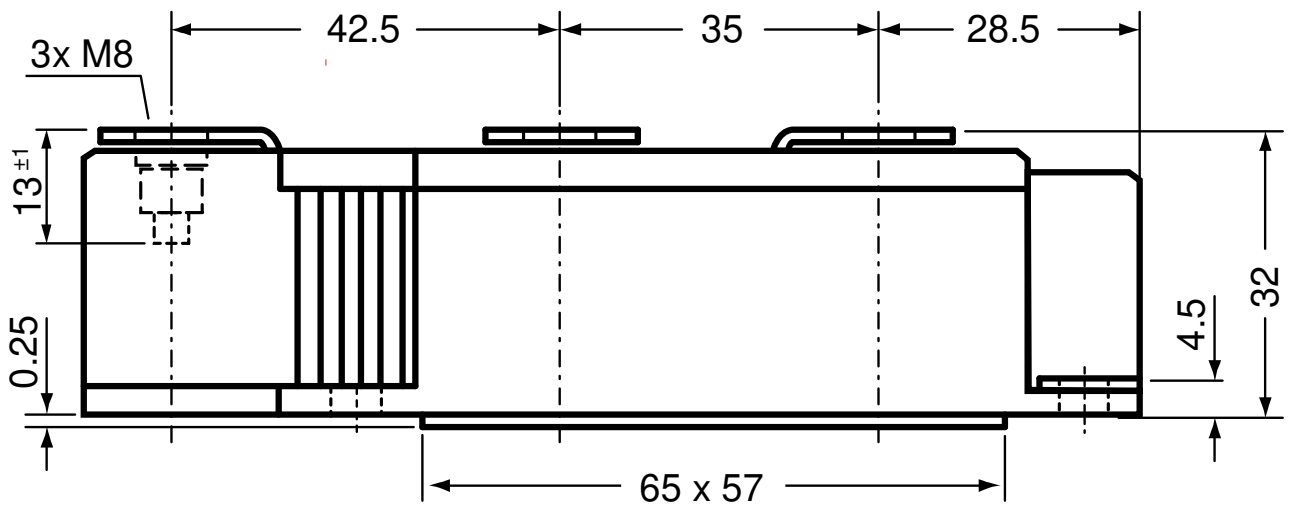


**Rectifier**

$V_{0\ max}$	threshold voltage	0.75	V
$R_{0\ max}$	slope resistance *	0.4	mΩ



Outlines Y2





**Rectifier**

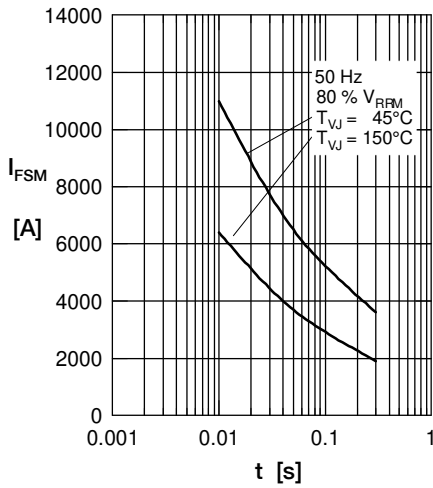


Fig. 1 Surge overload current  
 $I_{FSM}$ : Crest value,  $t$ : duration

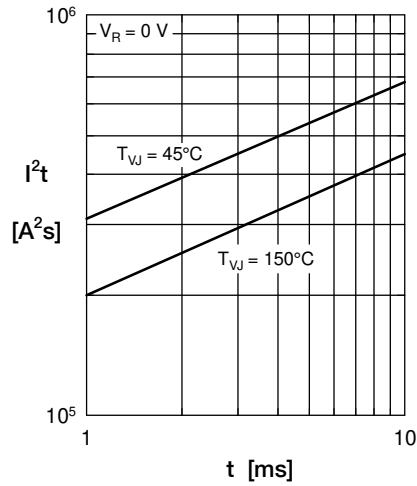


Fig. 2  $I^2t$  versus time (1-10 ms)

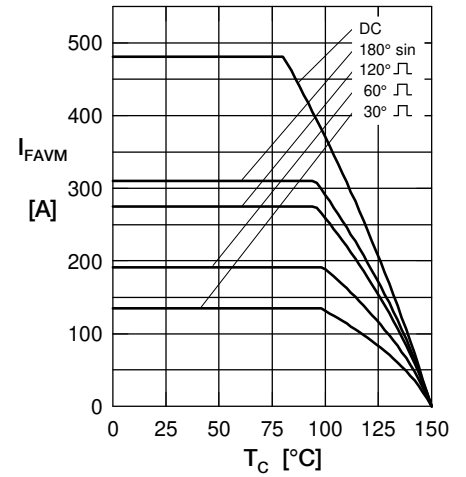


Fig. 3 Maximum forward current at case temperature

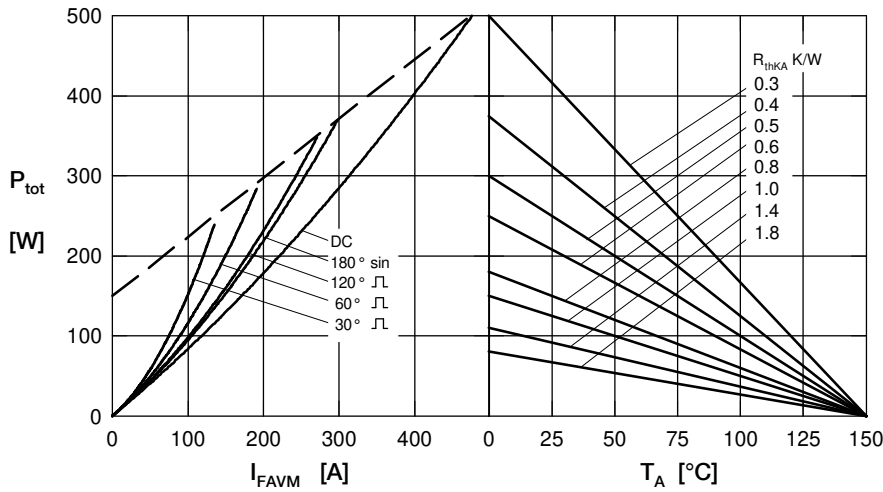


Fig. 4 Power dissipation versus forward current and ambient temperature (per diode)

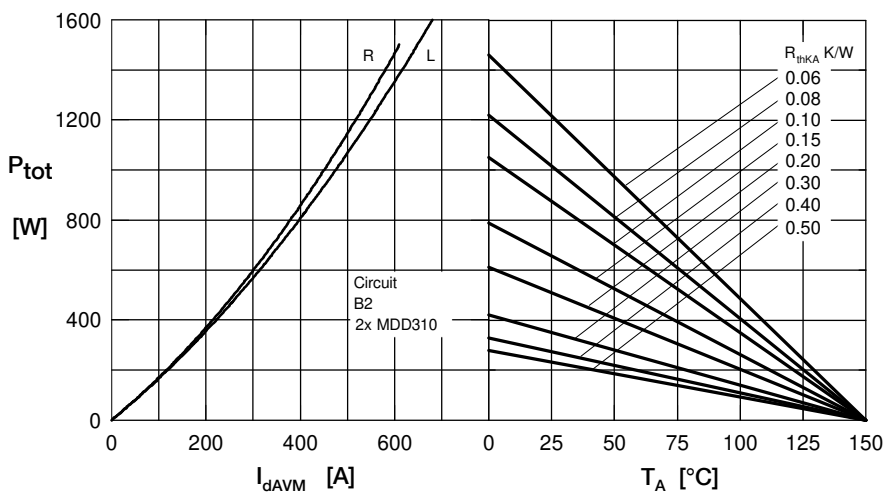


Fig. 5 Single phase rectifier bridge: Power dissipation vs. direct output current and ambient temperature  $R$  = resistive load,  $L$  = inductive load



**Rectifier**

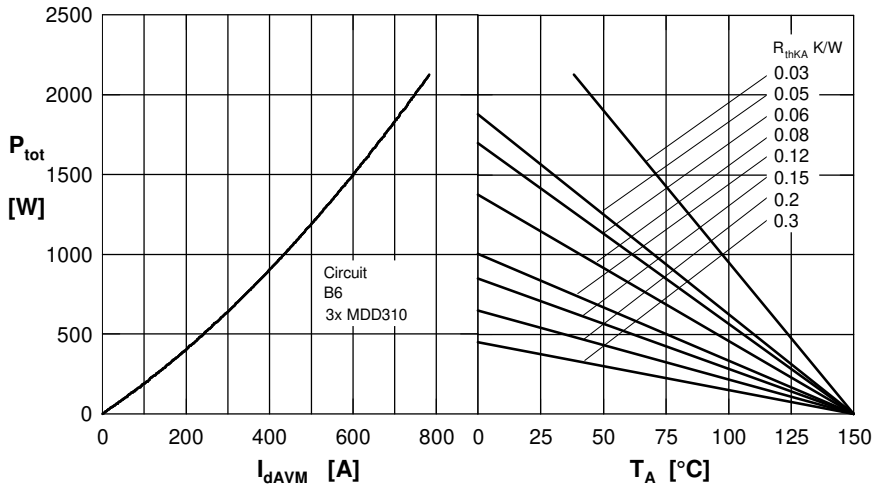


Fig.6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

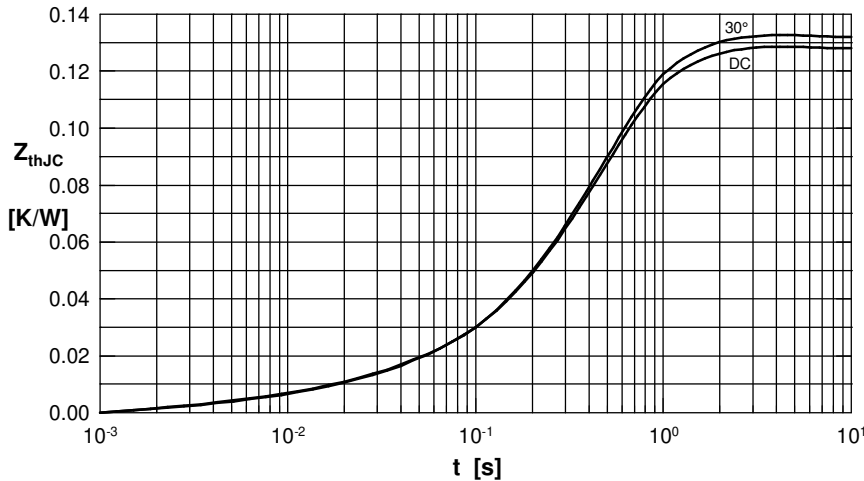


Fig. 7 Transient thermal impedance junction to case (per diode)

$R_{thJC}$  for various conduction angles  $d$ .

$d$	$R_{thJC}$ [K/W]
DC	0.129
180°	0.131
120°	0.132
60°	0.132
30°	0.133

Constants for  $Z_{thJC}$  calculation:

$i$	$R_{thi}$ [K/W]	$t_i$ [s]
1	0.0035	0.0099
2	0.0165	0.1680
3	0.1091	0.4560

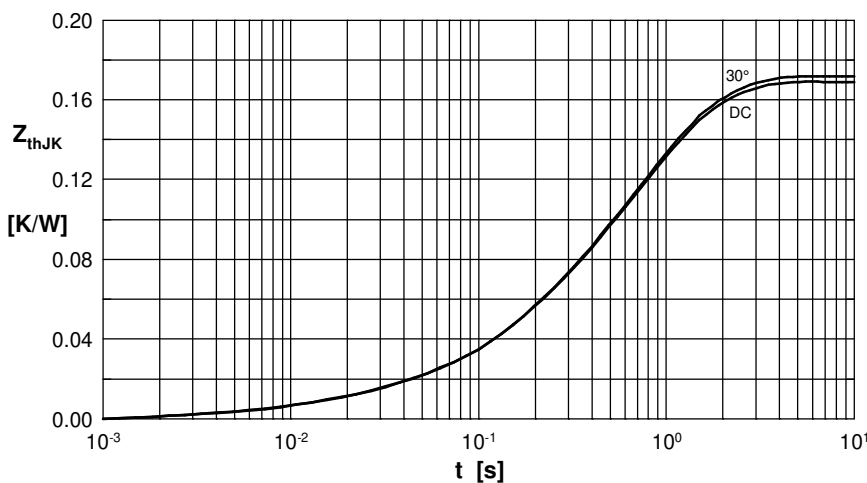


Fig. 8 Transient thermal impedance junction to heatsink (per diode)

$R_{thJK}$  for various conduction angles  $d$ .

$d$	$R_{thJK}$ [K/W]
DC	0.169
180°	0.171
120°	0.172
60°	0.172
30°	0.173

Constants for  $Z_{thJK}$  calculation:

$i$	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.0035	0.0099
2	0.0165	0.1680
3	0.1091	0.4560
4	0.0400	1.3600